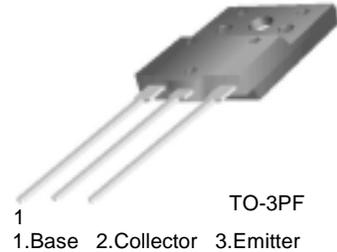


FAIRCHILD
SEMICONDUCTOR®

FJAF6810

High Voltage Color Display Horizontal Deflection Output

- High Collector-Base Breakdown Voltage : $BV_{CBO} = 1500V$
- High Switching Speed : $t_f(\text{typ.}) = 0.1\mu s$
- For Color Monitor



NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	750	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current (DC)	10	A
I_{CP}^*	Collector Current (Pulse)	20	A
P_C	Collector Dissipation	60	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ C$

* Pulse Test: Pulse Width=5ms, Duty Cycle $\leq 10\%$

Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector Cut-off Current	$V_{CB}=1400V, R_{BE}=0$			1	mA
I_{CBO}	Collector Cut-off Current	$V_{CB}=800V, I_E=0$			10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=4V, I_C=0$			1	mA
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=500\mu A, I_C=0$	6			V
h_{FE1}	DC Current Gain	$V_{CE}=5V, I_C=1A$	10			
h_{FE2}		$V_{CE}=5V, I_C=6A$	5		8	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C=6A, I_B=1.5A$			3	V
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage	$I_C=6A, I_B=1.5A$			1.5	V
t_{STG}^*	Storage Time	$V_{CC}=200V, I_C=6A, R_L=33\Omega$ $I_{B1}=1.2A, I_{B2}=-2.4A$			3	μs
t_F^*	Fall Time				0.2	μs

* Pulse Test: PW=20 μs , duty Cycle=1% Pulsed

Thermal Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.08	$^\circ C/W$